

METHOD OF EXTENDING THE AREAS OF CLEAR FIELD PHASE SHIFT GENERATION

ABSTRACT OF THE DISCLOSURE

An exemplary Full Phase patterning method involves patterning gates to increase process margins from conventional methods. This technique can define all poly patterns with a phase mask, using only a field or trim mask to resolve conflicts in the phase mask. The trim mask exposes a series of lines that either separates the different phase areas where patterns are not desired or minimizes the range of sizes of the phase patterns next to a critical gate area.

10016439-121401
TOTAL 639001